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### Understanding [Embedded - FPGAs \(Field Programmable Gate Array\)](#)

Embedded - FPGAs, or Field Programmable Gate Arrays, are advanced integrated circuits that offer unparalleled flexibility and performance for digital systems. Unlike traditional fixed-function logic devices, FPGAs can be programmed and reprogrammed to execute a wide array of logical operations, enabling customized functionality tailored to specific applications. This reprogrammability allows developers to iterate designs quickly and implement complex functions without the need for custom hardware.

### Applications of Embedded - FPGAs

The versatility of Embedded - FPGAs makes them indispensable in numerous fields. In telecommunications.

#### Details

Product Status	Active
Number of LABs/CLBs	-
Number of Logic Elements/Cells	-
Total RAM Bits	-
Number of I/O	49
Number of Gates	30000
Voltage - Supply	1.425V ~ 1.575V
Mounting Type	Surface Mount
Operating Temperature	0°C ~ 85°C (TJ)
Package / Case	68-VFQFN Exposed Pad
Supplier Device Package	68-QFN (8x8)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/a3p030-1qng68">https://www.e-xfl.com/product-detail/microchip-technology/a3p030-1qng68</a>

## I/Os with Advanced I/O Standards

The ProASIC3 family of FPGAs features a flexible I/O structure, supporting a range of voltages (1.5 V, 1.8 V, 2.5 V, and 3.3 V). ProASIC3 FPGAs support many different I/O standards—single-ended and differential.

The I/Os are organized into banks, with two or four banks per device. The configuration of these banks determines the I/O standards supported ([Table 1-1](#)).

**Table 1-1 • I/O Standards Supported**

I/O Bank Type	Device and Bank Location	I/O Standards Supported		
		LVTTL/ LVCMOS	PCI/PCI-X	LVPECL, LVDS, B-LVDS, M-LVDS
Advanced	East and west Banks of A3P250 and larger devices	✓	✓	✓
Standard Plus	North and south banks of A3P250 and larger devices All banks of A3P060 and A3P125	✓	✓	Not supported
Standard	All banks of A3P015 and A3P030	✓	Not supported	Not supported

Each I/O module contains several input, output, and enable registers. These registers allow the implementation of the following:

- Single-Data-Rate applications
- Double-Data-Rate applications—DDR LVDS, B-LVDS, and M-LVDS I/Os for point-to-point communications

ProASIC3 banks for the A3P250 device and above support LVPECL, LVDS, B-LVDS and M-LVDS. B-LVDS and M-LVDS can support up to 20 loads.

Hot-swap (also called hot-plug, or hot-insertion) is the operation of hot-insertion or hot-removal of a card in a powered-up system.

Cold-sparing (also called cold-swap) refers to the ability of a device to leave system data undisturbed when the system is powered up, while the component itself is powered down, or when power supplies are floating.

## Wide Range I/O Support

ProASIC3 devices support JEDEC-defined wide range I/O operation. ProASIC3 supports the JESD8-B specification, covering both 3 V and 3.3 V supplies, for an effective operating range of 2.7 V to 3.6 V.

Wider I/O range means designers can eliminate power supplies or power conditioning components from the board or move to less costly components with greater tolerances. Wide range eases I/O bank management and provides enhanced protection from system voltage spikes, while providing the flexibility to easily run custom voltage applications.

## Specifying I/O States During Programming

You can modify the I/O states during programming in FlashPro. In FlashPro, this feature is supported for PDB files generated from Designer v8.5 or greater. See the [FlashPro User's Guide](#) for more information.

**Note:** PDB files generated from Designer v8.1 to Designer v8.4 (including all service packs) have limited display of Pin Numbers only.

1. Load a PDB from the FlashPro GUI. You must have a PDB loaded to modify the I/O states during programming.
2. From the FlashPro GUI, click PDB Configuration. A FlashPoint – Programming File Generator window appears.
3. Click the Specify I/O States During Programming button to display the Specify I/O States During Programming dialog box.
4. Sort the pins as desired by clicking any of the column headers to sort the entries by that header. Select the I/Os you wish to modify ([Figure 1-4 on page 1-8](#)).
5. Set the I/O Output State. You can set Basic I/O settings if you want to use the default I/O settings for your pins, or use Custom I/O settings to customize the settings for each pin. Basic I/O state settings:
  - 1 – I/O is set to drive out logic High

**Table 2-11 • Summary of I/O Output Buffer Power (per pin) – Default I/O Software Settings<sup>1</sup>**  
**Applicable to Advanced I/O Banks**

	C <sub>LOAD</sub> (pF)	V <sub>CCI</sub> (V)	Static Power PDC3 (mW) <sup>2</sup>	Dynamic Power PAC10 (μW/MHz) <sup>3</sup>
<b>Single-Ended</b>				
3.3 V LVTTTL / 3.3 V LVCMOS	35	3.3	–	468.67
3.3 V LVCMOS Wide Range <sup>4</sup>	35	3.3	–	468.67
2.5 V LVCMOS	35	2.5	–	267.48
1.8 V LVCMOS	35	1.8	–	149.46
1.5 V LVCMOS (JESD8-11)	35	1.5	–	103.12
3.3 V PCI	10	3.3	–	201.02
3.3 V PCI-X	10	3.3	–	201.02
<b>Differential</b>				
LVDS	–	2.5	7.74	88.92
LVPECL	–	3.3	19.54	166.52

**Notes:**

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. PDC3 is the static power (where applicable) measured on VCCI.
3. PAC10 is the total dynamic power measured on VCC and VCCI.
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

**Table 2-12 • Summary of I/O Output Buffer Power (Per Pin) – Default I/O Software Settings<sup>1</sup>**  
**Applicable to Standard Plus I/O Banks**

	C <sub>LOAD</sub> (pF)	V <sub>CCI</sub> (V)	Static Power PDC3 (mW) <sup>2</sup>	Dynamic Power PAC10 (μW/MHz) <sup>3</sup>
<b>Single-Ended</b>				
3.3 V LVTTTL / 3.3 V LVCMOS	35	3.3	–	452.67
3.3 V LVCMOS Wide Range <sup>4</sup>	35	3.3	–	452.67
2.5 V LVCMOS	35	2.5	–	258.32
1.8 V LVCMOS	35	1.8	–	133.59
1.5 V LVCMOS (JESD8-11)	35	1.5	–	92.84
3.3 V PCI	10	3.3	–	184.92
3.3 V PCI-X	10	3.3	–	184.92

**Notes:**

1. Dynamic power consumption is given for standard load and software default drive strength and output slew.
2. P<sub>DC3</sub> is the static power (where applicable) measured on VMV.
3. P<sub>AC10</sub> is the total dynamic power measured on VCC and VMV.
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD8-B specification.

**Table 2-29 • I/O Output Buffer Maximum Resistances<sup>1</sup>**  
**Applicable to Standard Plus I/O Banks**

Standard	Drive Strength	R <sub>PULL-DOWN</sub> (Ω) <sup>2</sup>	R <sub>PULL-UP</sub> (Ω) <sup>3</sup>
3.3 V LVTTTL / 3.3 V LVCMOS	2 mA	100	300
	4 mA	100	300
	6 mA	50	150
	8 mA	50	150
	12 mA	25	75
	16 mA	25	75
3.3 V LVCMOS Wide Range <sup>4</sup>	100 μA	Same as regular 3.3 V LVCMOS	Same as regular 3.3 V LVCMOS
2.5 V LVCMOS	2 mA	100	200
	4 mA	100	200
	6 mA	50	100
	8 mA	50	100
	12 mA	25	50
1.8 V LVCMOS	2 mA	200	225
	4 mA	100	112
	6 mA	50	56
	8 mA	50	56
1.5 V LVCMOS	2 mA	200	224
	4 mA	100	112
3.3 V PCI/PCI-X	Per PCI/PCI-X specification	25	75

**Notes:**

1. These maximum values are provided for informational reasons only. Minimum output buffer resistance values depend on VCCI, drive strength selection, temperature, and process. For board design considerations and detailed output buffer resistances, use the corresponding IBIS models located at <http://www.microsemi.com/soc/download/ibis/default.aspx>.
2.  $R_{(PULL-DOWN-MAX)} = (VOL_{spec}) / IOL_{spec}$
3.  $R_{(PULL-UP-MAX)} = (VCCI_{max} - VOH_{spec}) / IOH_{spec}$
4. All LVCMOS 3.3 V software macros support LVCMOS 3.3 V wide range as specified in the JESD-8B specification.

**Table 2-55 • 3.3 V LVTTTL / 3.3 V LVCMOS Low Slew**  
**Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$ , Worst-Case  $V_{CCI} = 3.0\text{ V}$**   
**Applicable to Standard I/O Banks**

Drive Strength	Equiv. Software Default Drive Strength Option <sup>1</sup>	Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	$t_{EOUT}$	$t_{ZL}$	$t_{ZH}$	$t_{LZ}$	$t_{HZ}$	Units
100 $\mu\text{A}$	2 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		–1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		–2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 $\mu\text{A}$	4 mA	Std.	0.60	14.64	0.04	1.52	0.43	14.64	12.97	3.21	3.15	ns
		–1	0.51	12.45	0.04	1.29	0.36	12.45	11.04	2.73	2.68	ns
		–2	0.45	10.93	0.03	1.13	0.32	10.93	9.69	2.39	2.35	ns
100 $\mu\text{A}$	6 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		–1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		–2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns
100 $\mu\text{A}$	8 mA	Std.	0.60	10.16	0.04	1.52	0.43	10.16	9.08	3.71	3.98	ns
		–1	0.51	8.64	0.04	1.29	0.36	8.64	7.73	3.15	3.39	ns
		–2	0.45	7.58	0.03	1.13	0.32	7.58	6.78	2.77	2.97	ns

**Notes:**

1. The minimum drive strength for any LVCMOS 3.3 V software configuration when run in wide range is  $\pm 100\text{ }\mu\text{A}$ . Drive strength displayed in the software is supported for normal range only. For a detailed I/V curve, refer to the IBIS models.
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

## 1.8 V LVCMOS

Low-voltage CMOS for 1.8 V is an extension of the LVCMOS standard (JESD8-5) used for general-purpose 1.8 V applications. It uses a 1.8 V input buffer and a push-pull output buffer.

**Table 2-66 • Minimum and Maximum DC Input and Output Levels**  
Applicable to Advanced I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL <sup>1</sup>	IIH <sup>2</sup>
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA <sup>3</sup>	Max mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	2	2	11	9	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	4	4	22	17	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	6	6	44	35	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	8	8	51	45	10	10
12 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	12	12	74	91	10	10
16 mA	−0.3	0.35 * VCCI	0.65 * VCCI	1.9	0.45	VCCI − 0.45	16	16	74	91	10	10

**Notes:**

1. IIL is the input leakage current per I/O pin over recommended operation conditions where  $-0.3\text{ V} < V_{IN} < V_{IL}$ .
2. IIH is the input leakage current per I/O pin over recommended operating conditions  $V_{IH} < V_{IN} < V_{CCI}$ . Input current is larger when operating outside recommended ranges
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

**Table 2-67 • Minimum and Maximum DC Input and Output Levels**  
Applicable to Standard Plus I/O Banks

1.8 V LVCMOS	VIL		VIH		VOL	VOH	IOL	IOH	IOSL	IOSH	IIL <sup>1</sup>	IIH <sup>2</sup>
Drive Strength	Min V	Max V	Min V	Max V	Max V	Min V	mA	mA	Max mA <sup>3</sup>	Max mA <sup>3</sup>	μA <sup>4</sup>	μA <sup>4</sup>
2 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	2	2	11	9	10	10
4 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	4	4	22	17	10	10
6 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	6	6	44	35	10	10
8 mA	−0.3	0.35 * VCCI	0.65 * VCCI	3.6	0.45	VCCI − 0.45	8	8	44	35	10	10

**Notes:**

1. IIL is the input leakage current per I/O pin over recommended operation conditions where  $-0.3\text{ V} < V_{IN} < V_{IL}$ .
2. IIH is the input leakage current per I/O pin over recommended operating conditions  $V_{IH} < V_{IN} < V_{CCI}$ . Input current is larger when operating outside recommended ranges
3. Currents are measured at high temperature (100°C junction temperature) and maximum voltage.
4. Currents are measured at 85°C junction temperature.
5. Software default selection highlighted in gray.

**Table 2-93 • Minimum and Maximum DC Input and Output Levels**

DC Parameter	Description	Min.	Max.	Min.	Max.	Min.	Max.	Units
VCCI	Supply Voltage	3.0		3.3		3.6		V
VOL	Output Low Voltage	0.96	1.27	1.06	1.43	1.30	1.57	V
VOH	Output High Voltage	1.8	2.11	1.92	2.28	2.13	2.41	V
VIL, VIH	Input Low, Input High Voltages	0	3.6	0	3.6	0	3.6	V
VODIFF	Differential Output Voltage	0.625	0.97	0.625	0.97	0.625	0.97	V
VOCM	Output Common-Mode Voltage	1.762	1.98	1.762	1.98	1.762	1.98	V
VICM	Input Common-Mode Voltage	1.01	2.57	1.01	2.57	1.01	2.57	V
VIDIFF	Input Differential Voltage	300		300		300		mV

**Table 2-94 • AC Waveforms, Measuring Points, and Capacitive Loads**

Input Low (V)	Input High (V)	Measuring Point* (V)
1.64	1.94	Cross point

*Note:* \*Measuring point =  $V_{trip}$ . See [Table 2-22 on page 2-22](#) for a complete table of trip points.

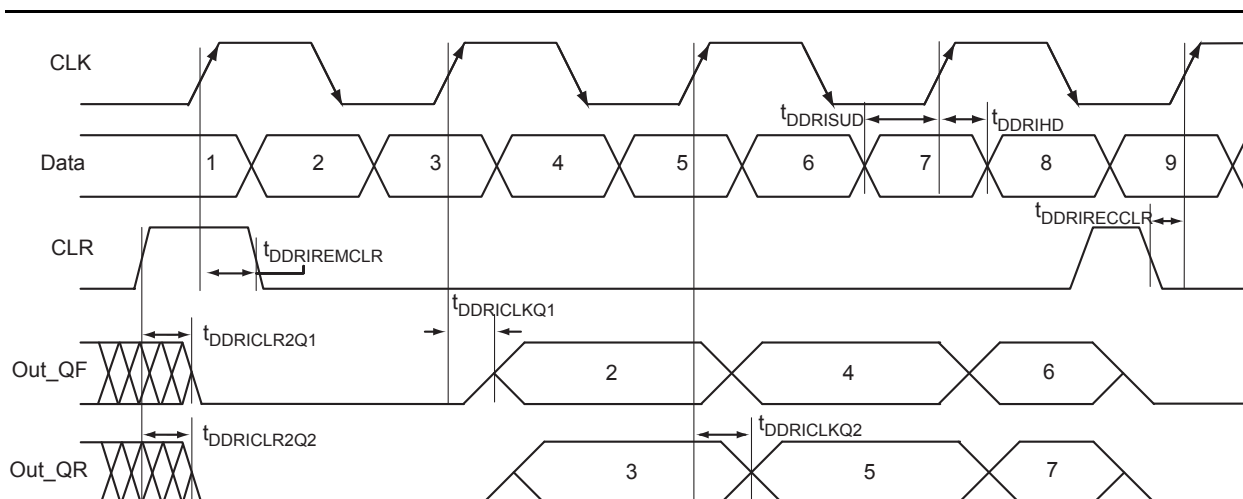
### Timing Characteristics

**Table 2-95 • LVPECL**

Commercial-Case Conditions:  $T_J = 70^{\circ}\text{C}$ , Worst-Case VCC = 1.425 V, Worst-Case VCCI = 3.0 V

Speed Grade	$t_{DOUT}$	$t_{DP}$	$t_{DIN}$	$t_{PY}$	Units
Std.	0.66	1.80	0.04	1.40	ns
–1	0.56	1.53	0.04	1.19	ns
–2	0.49	1.34	0.03	1.05	ns

*Note:* For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.



**Figure 2-21 • Input DDR Timing Diagram**

### Timing Characteristics

**Table 2-102 • Input DDR Propagation Delays**

Commercial-Case Conditions:  $T_J = 70^{\circ}\text{C}$ , Worst Case  $V_{CC} = 1.425\text{ V}$

Parameter	Description	-2	-1	Std.	Units
$t_{\text{DDRICKQ1}}$	Clock-to-Out Out_QR for Input DDR	0.27	0.31	0.37	ns
$t_{\text{DDRICKQ2}}$	Clock-to-Out Out_QF for Input DDR	0.39	0.44	0.52	ns
$t_{\text{DDRISUD}}$	Data Setup for Input DDR (Fall)	0.25	0.28	0.33	ns
	Data Setup for Input DDR (Rise)	0.25	0.28	0.33	ns
$t_{\text{DDRIHD}}$	Data Hold for Input DDR (Fall)	0.00	0.00	0.00	ns
	Data Hold for Input DDR (Rise)	0.00	0.00	0.00	ns
$t_{\text{DDRICLR2Q1}}$	Asynchronous Clear-to-Out Out_QR for Input DDR	0.46	0.53	0.62	ns
$t_{\text{DDRICLR2Q2}}$	Asynchronous Clear-to-Out Out_QF for Input DDR	0.57	0.65	0.76	ns
$t_{\text{DDRIEMCLR}}$	Asynchronous Clear Removal time for Input DDR	0.00	0.00	0.00	ns
$t_{\text{DDRIECCLR}}$	Asynchronous Clear Recovery time for Input DDR	0.22	0.25	0.30	ns
$t_{\text{DDRIWCLR}}$	Asynchronous Clear Minimum Pulse Width for Input DDR	0.22	0.25	0.30	ns
$t_{\text{DDRICKMPWH}}$	Clock Minimum Pulse Width High for Input DDR	0.36	0.41	0.48	ns
$t_{\text{DDRICKMPWL}}$	Clock Minimum Pulse Width Low for Input DDR	0.32	0.37	0.43	ns
$F_{\text{DDRIMAX}}$	Maximum Frequency for Input DDR	350	309	263	MHz

**Note:** For specific junction temperature and voltage-supply levels, refer to Table 2-6 on page 2-6 for derating values.



## Timing Characteristics

**Table 2-105 • Combinatorial Cell Propagation Delays**

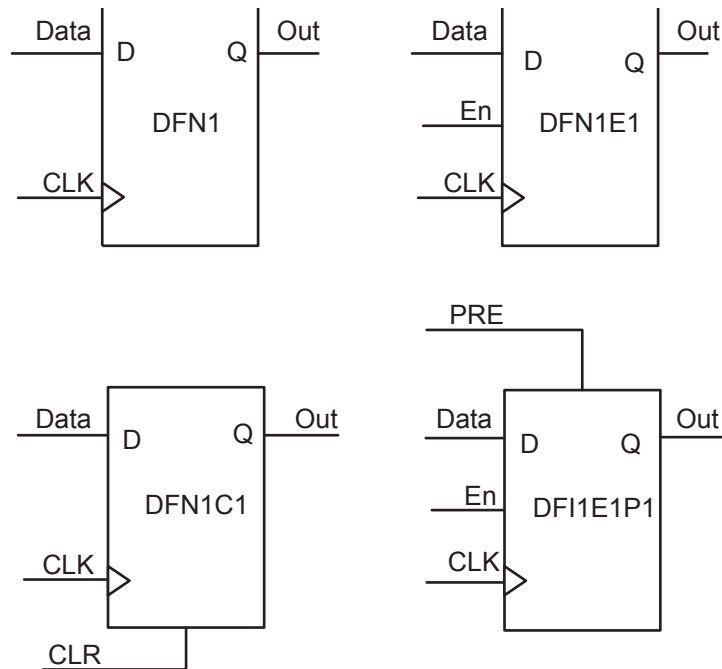
Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$

Combinatorial Cell	Equation	Parameter	-2	-1	Std.	Units
INV	$Y = !A$	$t_{PD}$	0.40	0.46	0.54	ns
AND2	$Y = A \cdot B$	$t_{PD}$	0.47	0.54	0.63	ns
NAND2	$Y = !(A \cdot B)$	$t_{PD}$	0.47	0.54	0.63	ns
OR2	$Y = A + B$	$t_{PD}$	0.49	0.55	0.65	ns
NOR2	$Y = !(A + B)$	$t_{PD}$	0.49	0.55	0.65	ns
XOR2	$Y = A \oplus B$	$t_{PD}$	0.74	0.84	0.99	ns
MAJ3	$Y = \text{MAJ}(A, B, C)$	$t_{PD}$	0.70	0.79	0.93	ns
XOR3	$Y = A \oplus B \oplus C$	$t_{PD}$	0.87	1.00	1.17	ns
MUX2	$Y = A !S + B S$	$t_{PD}$	0.51	0.58	0.68	ns
AND3	$Y = A \cdot B \cdot C$	$t_{PD}$	0.56	0.64	0.75	ns

**Note:** For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

## VersaTile Specifications as a Sequential Module

The ProASIC3 library offers a wide variety of sequential cells, including flip-flops and latches. Each has a data input and optional enable, clear, or preset. In this section, timing characteristics are presented for a representative sample from the library. For more details, refer to the [Fusion](#), [IGLOO/e](#), and [ProASIC3/E Macro Library Guide](#).



**Figure 2-26 • Sample of Sequential Cells**

## Timing Characteristics

**Table 2-107 • A3P015 Global Resource**  
 Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$

Parameter	Description	–2		–1		Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	Min. <sup>1</sup>	Max. <sup>2</sup>	Min. <sup>1</sup>	Max. <sup>2</sup>	
$t_{\text{RCKL}}$	Input Low Delay for Global Clock	0.66	0.81	0.75	0.92	0.88	1.08	ns
$t_{\text{RCKH}}$	Input High Delay for Global Clock	0.67	0.84	0.76	0.96	0.89	1.13	ns
$t_{\text{RCKMPWH}}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{\text{RCKMPWL}}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
$t_{\text{RCKSW}}$	Maximum Skew for Global Clock		0.18		0.21		0.25	ns

**Notes:**

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage-supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-108 • A3P030 Global Resource**  
 Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$

Parameter	Description	–2		–1		Std.		Units
		Min. <sup>1</sup>	Max. <sup>2</sup>	Min. <sup>1</sup>	Max. <sup>2</sup>	Min. <sup>1</sup>	Max. <sup>2</sup>	
$t_{\text{RCKL}}$	Input Low Delay for Global Clock	0.67	0.81	0.76	0.92	0.89	1.09	ns
$t_{\text{RCKH}}$	Input High Delay for Global Clock	0.68	0.85	0.77	0.97	0.91	1.14	ns
$t_{\text{RCKMPWH}}$	Minimum Pulse Width High for Global Clock	0.75		0.85		1.00		ns
$t_{\text{RCKMPWL}}$	Minimum Pulse Width Low for Global Clock	0.85		0.96		1.13		ns
$t_{\text{RCKSW}}$	Maximum Skew for Global Clock		0.18		0.21		0.24	ns

**Notes:**

1. Value reflects minimum load. The delay is measured from the CCC output to the clock pin of a sequential element, located in a lightly loaded row (single element is connected to the global net).
2. Value reflects maximum load. The delay is measured on the clock pin of the farthest sequential element, located in a fully loaded row (all available flip-flops are connected to the global net in the row).
3. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-117 • RAM512X18****Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ , Worst-Case  $V_{CC} = 1.425\text{ V}$** 

Parameter	Description	-2	-1	Std.	Units
$t_{AS}$	Address setup time	0.25	0.28	0.33	ns
$t_{AH}$	Address hold time	0.00	0.00	0.00	ns
$t_{ENS}$	REN, WEN setup time	0.13	0.15	0.17	ns
$t_{ENH}$	REN, WEN hold time	0.10	0.11	0.13	ns
$t_{DS}$	Input data (WD) setup time	0.18	0.21	0.25	ns
$t_{DH}$	Input data (WD) hold time	0.00	0.00	0.00	ns
$t_{CKQ1}$	Clock High to new data valid on RD (output retained)	2.16	2.46	2.89	ns
$t_{CKQ2}$	Clock High to new data valid on RD (pipelined)	0.90	1.02	1.20	ns
$t_{C2CRWH}^1$	Address collision clk-to-clk delay for reliable read access after write on same address—Applicable to Opening Edge	0.50	0.43	0.38	ns
$t_{C2CWRH}^1$	Address collision clk-to-clk delay for reliable write access after read on same address—Applicable to Opening Edge	0.59	0.50	0.44	ns
$t_{RSTBQ}$	RESET Low to data out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to data out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{REMRSTB}$	RESET removal	0.29	0.33	0.38	ns
$t_{RECRSTB}$	RESET recovery	1.50	1.71	2.01	ns
$t_{MPWRSTB}$	RESET minimum pulse width	0.21	0.24	0.29	ns
$t_{CYC}$	Clock cycle time	3.23	3.68	4.32	ns
$F_{MAX}$	Maximum frequency	310	272	231	MHz

**Notes:**

1. For more information, refer to the application note [Simultaneous Read-Write Operations in Dual-Port SRAM for Flash-Based cSoCs and FPGAs](#).
2. For specific junction temperature and voltage supply levels, refer to [Table 2-6 on page 2-6](#) for derating values.

**Table 2-119 • FIFO (for A3P250 only, aspect-ratio-dependent)**  
**Worst Commercial-Case Conditions:  $T_J = 70^\circ\text{C}$ ,  $V_{CC} = 1.425\text{ V}$**

Parameter	Description	-2	-1	Std.	Units
$t_{\text{ENS}}$	REN, WEN Setup Time	3.26	3.71	4.36	ns
$t_{\text{ENH}}$	REN, WEN Hold Time	0.00	0.00	0.00	ns
$t_{\text{BKS}}$	BLK Setup Time	0.19	0.22	0.26	ns
$t_{\text{BKH}}$	BLK Hold Time	0.00	0.00	0.00	ns
$t_{\text{DS}}$	Input Data (WD) Setup Time	0.18	0.21	0.25	ns
$t_{\text{DH}}$	Input Data (WD) Hold Time	0.00	0.00	0.00	ns
$t_{\text{CKQ1}}$	Clock High to New Data Valid on RD (flow-through)	2.17	2.47	2.90	ns
$t_{\text{CKQ2}}$	Clock High to New Data Valid on RD (pipelined)	0.94	1.07	1.26	ns
$t_{\text{RCKEF}}$	RCLK High to Empty Flag Valid	1.72	1.96	2.30	ns
$t_{\text{WCKFF}}$	WCLK High to Full Flag Valid	1.63	1.86	2.18	ns
$t_{\text{CKAF}}$	Clock High to Almost Empty/Full Flag Valid	6.19	7.05	8.29	ns
$t_{\text{RSTFG}}$	RESET Low to Empty/Full Flag Valid	1.69	1.93	2.27	ns
$t_{\text{RSTAF}}$	RESET Low to Almost Empty/Full Flag Valid	6.13	6.98	8.20	ns
$t_{\text{RSTBQ}}$	RESET Low to Data Out Low on RD (flow-through)	0.92	1.05	1.23	ns
	RESET Low to Data Out Low on RD (pipelined)	0.92	1.05	1.23	ns
$t_{\text{REMRSTB}}$	RESET Removal	0.29	0.33	0.38	ns
$t_{\text{RECRSTB}}$	RESET Recovery	1.50	1.71	2.01	ns
$t_{\text{MPWRSTB}}$	RESET Minimum Pulse Width	0.21	0.24	0.29	ns
$t_{\text{CYC}}$	Clock Cycle Time	3.23	3.68	4.32	ns
$F_{\text{MAX}}$	Maximum Frequency for FIFO	310	272	231	MHz

mode is not used in the design, the FF pin is available as a regular I/O. For IGLOOe, ProASIC3EL, and RT ProASIC3 only, the FF pin can be configured as a Schmitt trigger input.

When Flash\*Freeze mode is used, the FF pin must not be left floating to avoid accidentally entering Flash\*Freeze mode. While in Flash\*Freeze mode, the Flash\*Freeze pin should be constantly asserted.

The Flash\*Freeze pin can be used with any single-ended I/O standard supported by the I/O bank in which the pin is located, and input signal levels compatible with the I/O standard selected. The FF pin should be treated as a sensitive asynchronous signal. When defining pin placement and board layout, simultaneously switching outputs (SSOs) and their effects on sensitive asynchronous pins must be considered.

Unused FF or I/O pins are tristated with weak pull-up. This default configuration applies to both Flash\*Freeze mode and normal operation mode. No user intervention is required.

## JTAG Pins

Low power flash devices have a separate bank for the dedicated JTAG pins. The JTAG pins can be run at any voltage from 1.5 V to 3.3 V (nominal). VCC must also be powered for the JTAG state machine to operate, even if the device is in bypass mode; VJTAG alone is insufficient. Both VJTAG and VCC to the part must be supplied to allow JTAG signals to transition the device. Isolating the JTAG power supply in a separate I/O bank gives greater flexibility in supply selection and simplifies power supply and PCB design. If the JTAG interface is neither used nor planned for use, the VJTAG pin together with the TRST pin could be tied to GND.

### TCK Test Clock

Test clock input for JTAG boundary scan, ISP, and UJTAG. The TCK pin does not have an internal pull-up/-down resistor. If JTAG is not used, Microsemi recommends tying off TCK to GND through a resistor placed close to the FPGA pin. This prevents JTAG operation in case TMS enters an undesired state.

Note that to operate at all VJTAG voltages, 500  $\Omega$  to 1 k $\Omega$  will satisfy the requirements. Refer to [Table 1](#) for more information.

**Table 1 • Recommended Tie-Off Values for the TCK and TRST Pins**

VJTAG	Tie-Off Resistance
3.3 V	200 $\Omega$ –1 k $\Omega$
2.5 V	200 $\Omega$ –1 k $\Omega$
1.8 V	500 $\Omega$ –1 k $\Omega$
1.5 V	500 $\Omega$ –1 k $\Omega$

#### Notes:

1. Equivalent parallel resistance if more than one device is on the JTAG chain
2. The TCK pin can be pulled up/down.
3. The TRST pin is pulled down.

### TDI Test Data Input

Serial input for JTAG boundary scan, ISP, and UJTAG usage. There is an internal weak pull-up resistor on the TDI pin.

### TDO Test Data Output

Serial output for JTAG boundary scan, ISP, and UJTAG usage.

### TMS Test Mode Select

The TMS pin controls the use of the IEEE 1532 boundary scan pins (TCK, TDI, TDO, TRST). There is an internal weak pull-up resistor on the TMS pin.

### TRST Boundary Scan Reset Pin

The TRST pin functions as an active low input to asynchronously initialize (or reset) the boundary scan circuitry. There is an internal weak pull-up resistor on the TRST pin. If JTAG is not used, an external pull-down resistor could be included to ensure the test access port (TAP) is held in reset mode. The resistor values must be chosen from [Table 1](#) and must satisfy the parallel resistance value requirement. The values in [Table 1](#) correspond to the resistor recommended when a single device is used, and the equivalent parallel resistor when multiple devices are connected via a JTAG chain.

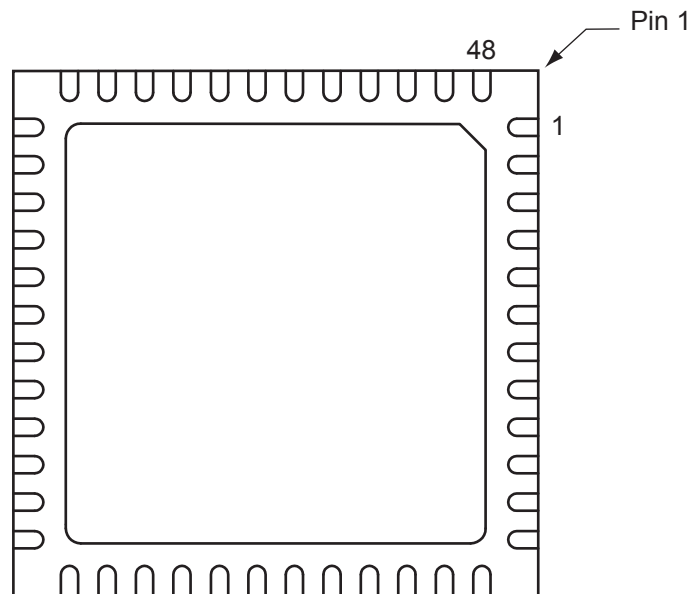
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## 4 – Package Pin Assignments

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### QN48 – Bottom View

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*Note:* The die attach paddle center of the package is tied to ground (GND).

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#### **Note**

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

QN132	
Pin Number	A3P060 Function
A1	GAB2/IO00RSB1
A2	IO93RSB1
A3	VCCIB1
A4	GFC1/IO89RSB1
A5	GFB0/IO86RSB1
A6	VCCPLF
A7	GFA1/IO84RSB1
A8	GFC2/IO81RSB1
A9	IO78RSB1
A10	VCC
A11	GEB1/IO75RSB1
A12	GEA0/IO72RSB1
A13	GEC2/IO69RSB1
A14	IO65RSB1
A15	VCC
A16	IO64RSB1
A17	IO63RSB1
A18	IO62RSB1
A19	IO61RSB1
A20	IO58RSB1
A21	GDB2/IO55RSB1
A22	NC
A23	GDA2/IO54RSB1
A24	TDI
A25	TRST
A26	GDC1/IO48RSB0
A27	VCC
A28	IO47RSB0
A29	GCC2/IO46RSB0
A30	GCA2/IO44RSB0
A31	GCA0/IO43RSB0
A32	GCB1/IO40RSB0
A33	IO36RSB0
A34	VCC
A35	IO31RSB0
A36	GBA2/IO28RSB0

QN132	
Pin Number	A3P060 Function
A37	GBB1/IO25RSB0
A38	GBC0/IO22RSB0
A39	VCCIB0
A40	IO21RSB0
A41	IO18RSB0
A42	IO15RSB0
A43	IO14RSB0
A44	IO11RSB0
A45	GAB1/IO08RSB0
A46	NC
A47	GAB0/IO07RSB0
A48	IO04RSB0
B1	IO01RSB1
B2	GAC2/IO94RSB1
B3	GND
B4	GFC0/IO88RSB1
B5	VCOMPLF
B6	GND
B7	GFB2/IO82RSB1
B8	IO79RSB1
B9	GND
B10	GEB0/IO74RSB1
B11	VMV1
B12	GEB2/IO70RSB1
B13	IO67RSB1
B14	GND
B15	NC
B16	NC
B17	GND
B18	IO59RSB1
B19	GDC2/IO56RSB1
B20	GND
B21	GNDQ
B22	TMS
B23	TDO
B24	GDC0/IO49RSB0

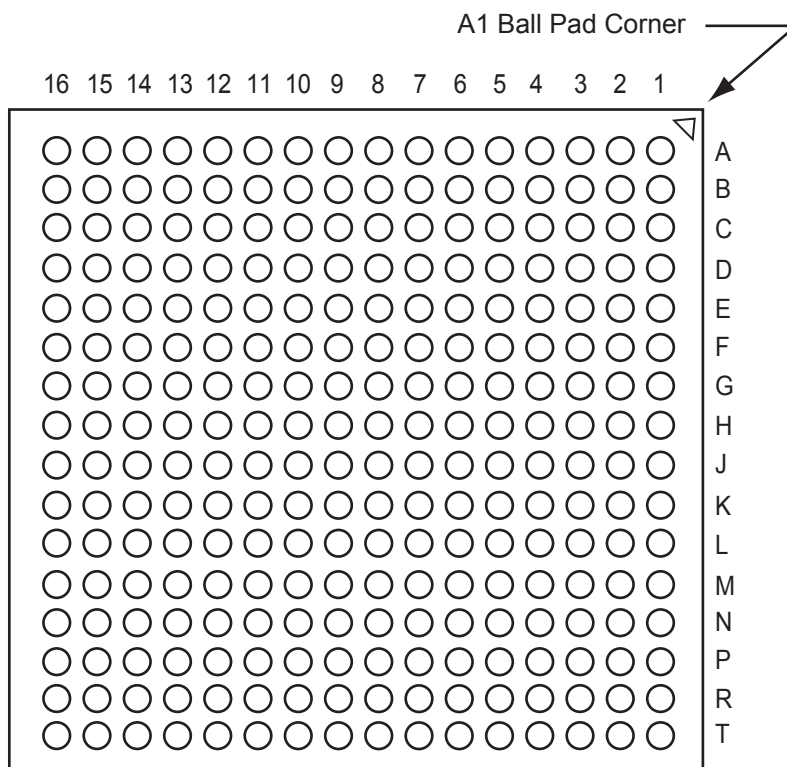
QN132	
Pin Number	A3P060 Function
B25	GND
B26	NC
B27	GCB2/IO45RSB0
B28	GND
B29	GCB0/IO41RSB0
B30	GCC1/IO38RSB0
B31	GND
B32	GBB2/IO30RSB0
B33	VMV0
B34	GBA0/IO26RSB0
B35	GBC1/IO23RSB0
B36	GND
B37	IO20RSB0
B38	IO17RSB0
B39	GND
B40	IO12RSB0
B41	GAC0/IO09RSB0
B42	GND
B43	GAA1/IO06RSB0
B44	GNDQ
C1	GAA2/IO02RSB1
C2	IO95RSB1
C3	VCC
C4	GFB1/IO87RSB1
C5	GFA0/IO85RSB1
C6	GFA2/IO83RSB1
C7	IO80RSB1
C8	VCCIB1
C9	GEA1/IO73RSB1
C10	GNDQ
C11	GEA2/IO71RSB1
C12	IO68RSB1
C13	VCCIB1
C14	NC
C15	NC
C16	IO60RSB1

TQ144	
Pin Number	A3P060 Function
109	NC
110	NC
111	GBA1/IO24RSB0
112	GBA0/IO23RSB0
113	GBB1/IO22RSB0
114	GBB0/IO21RSB0
115	GBC1/IO20RSB0
116	GBC0/IO19RSB0
117	VCCIB0
118	GND
119	VCC
120	IO18RSB0
121	IO17RSB0
122	IO16RSB0
123	IO15RSB0
124	IO14RSB0
125	IO13RSB0
126	IO12RSB0
127	IO11RSB0
128	NC
129	IO10RSB0
130	IO09RSB0
131	IO08RSB0
132	GAC1/IO07RSB0
133	GAC0/IO06RSB0
134	NC
135	GND
136	NC
137	GAB1/IO05RSB0
138	GAB0/IO04RSB0
139	GAA1/IO03RSB0
140	GAA0/IO02RSB0
141	IO01RSB0
142	IO00RSB0
143	GNDQ
144	VMV0



## FG256 – Bottom View

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### Note

For more information on package drawings, see [PD3068: Package Mechanical Drawings](#).

FG256	
Pin Number	A3P1000 Function
A1	GND
A2	GAA0/IO00RSB0
A3	GAA1/IO01RSB0
A4	GAB0/IO02RSB0
A5	IO16RSB0
A6	IO22RSB0
A7	IO28RSB0
A8	IO35RSB0
A9	IO45RSB0
A10	IO50RSB0
A11	IO55RSB0
A12	IO61RSB0
A13	GBB1/IO75RSB0
A14	GBA0/IO76RSB0
A15	GBA1/IO77RSB0
A16	GND
B1	GAB2/IO224PDB3
B2	GAA2/IO225PDB3
B3	GNDQ
B4	GAB1/IO03RSB0
B5	IO17RSB0
B6	IO21RSB0
B7	IO27RSB0
B8	IO34RSB0
B9	IO44RSB0
B10	IO51RSB0
B11	IO57RSB0
B12	GBC1/IO73RSB0
B13	GBB0/IO74RSB0
B14	IO71RSB0
B15	GBA2/IO78PDB1
B16	IO81PDB1
C1	IO224NDB3
C2	IO225NDB3
C3	VMV3
C4	IO11RSB0
C5	GAC0/IO04RSB0
C6	GAC1/IO05RSB0

FG256	
Pin Number	A3P1000 Function
C7	IO25RSB0
C8	IO36RSB0
C9	IO42RSB0
C10	IO49RSB0
C11	IO56RSB0
C12	GBC0/IO72RSB0
C13	IO62RSB0
C14	VMV0
C15	IO78NDB1
C16	IO81NDB1
D1	IO222NDB3
D2	IO222PDB3
D3	GAC2/IO223PDB3
D4	IO223NDB3
D5	GNDQ
D6	IO23RSB0
D7	IO29RSB0
D8	IO33RSB0
D9	IO46RSB0
D10	IO52RSB0
D11	IO60RSB0
D12	GNDQ
D13	IO80NDB1
D14	GBB2/IO79PDB1
D15	IO79NDB1
D16	IO82NSB1
E1	IO217PDB3
E2	IO218PDB3
E3	IO221NDB3
E4	IO221PDB3
E5	VMV0
E6	VCCIB0
E7	VCCIB0
E8	IO38RSB0
E9	IO47RSB0
E10	VCCIB0
E11	VCCIB0
E12	VMV1

FG256	
Pin Number	A3P1000 Function
E13	GBC2/IO80PDB1
E14	IO83PPB1
E15	IO86PPB1
E16	IO87PDB1
F1	IO217NDB3
F2	IO218NDB3
F3	IO216PDB3
F4	IO216NDB3
F5	VCCIB3
F6	GND
F7	VCC
F8	VCC
F9	VCC
F10	VCC
F11	GND
F12	VCCIB1
F13	IO83NPB1
F14	IO86NPB1
F15	IO90PPB1
F16	IO87NDB1
G1	IO210PSB3
G2	IO213NDB3
G3	IO213PDB3
G4	GFC1/IO209PPB3
G5	VCCIB3
G6	VCC
G7	GND
G8	GND
G9	GND
G10	GND
G11	VCC
G12	VCCIB1
G13	GCC1/IO91PPB1
G14	IO90NPB1
G15	IO88PDB1
G16	IO88NDB1
H1	GFB0/IO208NPB3
H2	GFA0/IO207NDB3

Revision	Changes	Page
<b>Revision 5 (Aug 2008)</b> DC and Switching Characteristics v1.3	T <sub>J</sub> , Maximum Junction Temperature, was changed to 100° from 110° in the "Thermal Characteristics" section and EQ 1. The calculated result of Maximum Power Allowed has thus changed to 1.463 W from 1.951 W.	2-6
	Values for the A3P015 device were added to Table 2-7 • Quiescent Supply Current Characteristics.	2-7
	Values for the A3P015 device were added to Table 2-14 • Different Components Contributing to Dynamic Power Consumption in ProASIC3 Devices. P <sub>AC14</sub> was removed. Table 2-15 • Different Components Contributing to the Static Power Consumption in ProASIC3 Devices is new.	2-11, 2-12
	The "PLL Contribution—P <sub>PLL</sub> " section was updated to change the P <sub>PLL</sub> formula from P <sub>AC13</sub> + P <sub>AC14</sub> * F <sub>CLKOUT</sub> to P <sub>DC4</sub> + P <sub>AC13</sub> * F <sub>CLKOUT</sub> .	2-14
	Both fall and rise values were included for t <sub>DDRISUD</sub> and t <sub>DDRIHD</sub> in Table 2-102 • Input DDR Propagation Delays.	2-78
	Table 2-107 • A3P015 Global Resource is new.	2-86
	The typical value for Delay Increments in Programmable Delay Blocks was changed from 160 to 200 in Table 2-115 • ProASIC3 CCC/PLL Specification.	2-90
<b>Revision 4 (Jun 2008)</b> DC and Switching Characteristics v1.2	Table note references were added to Table 2-2 • Recommended Operating Conditions 1, and the order of the table notes was changed.	2-2
	The title for Table 2-4 • Overshoot and Undershoot Limits 1 was modified to remove "as measured on quiet I/Os." Table note 1 was revised to remove "estimated SSO density over cycles." Table note 2 was revised to remove "refers only to overshoot/undershoot limits for simultaneous switching I/Os."	2-3
	The "Power per I/O Pin" section was updated to include 3 additional tables pertaining to input buffer power and output buffer power.	2-7
	Table 2-29 • I/O Output Buffer Maximum Resistances 1 was revised to include values for 3.3 V PCI/PCI-X.	2-27
	Table 2-90 • LVDS Minimum and Maximum DC Input and Output Levels was updated.	2-66
<b>Revision 3 (Jun 2008)</b> Packaging v1.3	Pin numbers were added to the "QN68 – Bottom View" package diagram. Note 2 was added below the diagram.	4-3
	The "QN132 – Bottom View" package diagram was updated to include D1 to D4. In addition, note 1 was changed from top view to bottom view, and note 2 is new.	4-6
<b>Revision 2 (Feb 2008)</b> Product Brief v1.0	This document was divided into two sections and given a version number, starting at v1.0. The first section of the document includes features, benefits, ordering information, and temperature and speed grade offerings. The second section is a device family overview.	N/A
	This document was updated to include A3P015 device information. QN68 is a new package that was added because it is offered in the A3P015. The following sections were updated: "Features and Benefits" "ProASIC3 Ordering Information" "Temperature Grade Offerings" "ProASIC3 Flash Family FPGAs" "A3P015 and A3P030" note Introduction and Overview (NA)	N/A

Revision	Changes	Page
<b>Revision 2 (cont'd)</b>	The "ProASIC3 FPGAs Package Sizes Dimensions" table is new.	III
	In the "ProASIC3 Ordering Information", the QN package measurements were updated to include both 0.4 mm and 0.5 mm.	IV
	In the General Description section the number of I/Os was updated from 288 to 300.	1-1
	The "QN68 – Bottom View" section is new.	4-3
Packaging v1.2		
<b>Revision 1 (Feb 2008)</b> DC and Switching Characteristics v1.1	In Table 2-2 • Recommended Operating Conditions 1, $T_J$ was listed in the symbol column and was incorrect. It was corrected and changed to $T_A$ .	2-2
	In Table 2-3 • Flash Programming Limits – Retention, Storage and Operating Temperature, Maximum Operating Junction Temperature was changed from 110°C to 100°C for both commercial and industrial grades.	2-3
	The "PLL Behavior at Brownout Condition" section is new.	2-4
	In the "PLL Contribution—PPLL" section, the following was deleted: FCLKIN is the input clock frequency.	2-14
	In Table 2-21 • Summary of Maximum and Minimum DC Input Levels, the note was incorrect. It previously said $T_J$ and it was corrected and changed to $T_A$ .	2-21
	In Table 2-115 • ProASIC3 CCC/PLL Specification, the SCLK parameter and note 1 are new.	2-90
	Table 2-125 • JTAG 1532 was populated with the parameter data, which was not in the previous version of the document.	2-108
	In the "VQ100" A3P030 pin table, the function of pin 63 was incorrect and changed from IO39RSB0 to GDB0/IO38RSB0.	4-19
Packaging v1.1		
<b>Revision 0 (Jan 2008)</b>	This document was previously in datasheet v2.2. As a result of moving to the handbook format, Actel has restarted the version numbers.	N/A
v2.2 (July 2007)	The M7 and M1 device part numbers have been updated in Table 1 • ProASIC3 Product Family, "I/Os Per Package", "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix".	i, ii, iii, iii, iv
	The words "ambient temperature" were added to the temperature range in the "Automotive ProASIC3 Ordering Information", "Temperature Grade Offerings", and "Speed Grade and Temperature Grade Matrix" sections.	iii, iv
	The $T_J$ parameter in Table 3-2 • Recommended Operating Conditions was changed to $T_A$ , ambient temperature, and table notes 4–6 were added.	3-2
v2.1 (May 2007)	In the "Clock Conditioning Circuit (CCC) and PLL" section, the Wide Input Frequency Range (1.5 MHz to 200 MHz) was changed to (1.5 MHz to 350 MHz).	i
	The "Clock Conditioning Circuit (CCC) and PLL" section was updated.	i
	In the "I/Os Per Package" section, the A3P030, A3P060, A3P125, ACP250, and A3P600 device I/Os were updated.	ii
	Table 3-5 • Package Thermal Resistivities was updated with A3P1000 information. The note below the table is also new.	3-5

Revision	Changes	Page
Advance v0.2, (continued)	Table 2-43 was updated.	2-64
	Table 2-18 was updated.	2-45
	Pin descriptions in the "JTAG Pins" section were updated.	2-51
	The "User I/O Naming Convention" section was updated.	2-48
	Table 3-7 was updated.	3-6
	The "Methodology" section was updated.	3-10
	Table 3-40 and Table 3-39 were updated.	3-33,3-32
	The A3P250 "100-Pin VQFP*" pin table was updated.	4-14
	The A3P250 "208-Pin PQFP*" pin table was updated.	4-23
	The A3P1000 "208-Pin PQFP*" pin table was updated.	4-29
	The A3P250 "144-Pin FBGA*" pin table was updated.	4-36
	The A3P1000 "144-Pin FBGA*" pin table was updated.	4-32
	The A3P250 "256-Pin FBGA*" pin table was updated.	4-45
	The A3P1000 "256-Pin FBGA*" pin table was updated.	4-54
	The A3P1000 "484-Pin FBGA*" pin table was updated.	4-68